



These specifications represent typical minimum performance. Actual results may vary. Maximum operating temperature for Ge is 80°C, all others are 110°C. Other materials, including sapphire, CsI and MgF and custom specifications available upon request.

Part Number	GS12000	GS12700	GS12800	GS12900	GS12950
Substrate	KRS-5	CaF ₂	BaF ₂	Ge	ZnSe
Spectral Range (μm)	2 - 35	1 - 10	1 - 12.5	8 - 12	1 - 15
Grid Period (μm)	0.25	0.25	0.25	0.4	0.25
OD (mm)	34.9	34.9	34.9	34.9	34.9
CA (mm)	25	25	25	25	25
t (mm)	7.9	7.9	7.9	7.9	7.9
Transmission Efficiency % (K1)					
2.5 μm	72	89	88		76
5.0 μm	84	88	88		85
8.0 μm				87	
10.0 μm	75	50	84	91	74
Transmission of Unwanted Radiation % (K2)					
2.5 μm	1.50	1.00	1.10		1.40
5.0 μm	0.50	0.28	0.30		0.50
8.0 μm				0.35	
10.0 μm	0.23	0.10	0.20	0.25	0.20
Degree of Polarization % (K1-K2)/(K1+K2)					
2.5 μm	95.8	97.8	97.5		96.3
5.0 μm	98.8	99.3	99.3		98.8
8.0 μm				99.2	
10.0 μm	99.7	99.6	99.5	99.4	99.4
Extinction Ratio expressed as K1/K2					
2.5 μm	48:1	89:1	80:1		54:1
5.0 μm	168:1	314:1	293:1		170:1
8.0 μm				249:1	
10.0 μm	326:1	500:1	420:1	364:1	370:1